

LC²MOS Quad SPST Switches

ADG221/ADG222

FEATURES

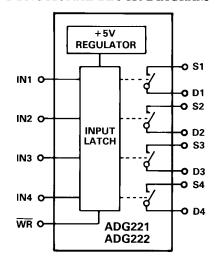
44V Supply Maximum Rating
± 15V Analog Signal Range
Low R_{ON} (60Ω)
Low Leakage (0.5nA)
Break-Before-Make Switching
Extended Plastic Temperature Range
(-40°C to +85°C)
Low Power Dissipation (25.5mW)
μP, TTL, CMOS Compatible
Available in 16-Lead DIP/SOIC and
20-Lead PLCC/LCCC Packages
Surface Mount Packages
Superior DG221 Replacement

GENERAL DESCRIPTION

The ADG221 and ADG222 are monolithic CMOS devices comprising four independently selectable switches. On-chip latches facilitate microprocessor interfacing. They are designed on an enhanced LC²MOS process which gives an increased signal handling capability of $\pm\,15V$. These switches also feature high switching speeds and low $R_{\rm ON}$.

The ADG221 and ADG222 consist of four SPST switches. They differ only in that the digital control logic is inverted. All devices exhibit break before make switching action. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

FUNCTIONAL BLOCK DIAGRAM



PRODUCT HIGHLIGHTS

1. Easily Interfaced:

Digital inputs are latched with a WR signal for microprocessor interfacing. A 5V regulated supply is internally generated permitting wider tolerances on the supplies without affecting the TTL digital input switching levels.

2. Single Supply Operation:

For applications where the analog signal is unipolar (0V to 15V), the switches can be operated from a single +15V supply.

3. Low Leakage:

Leakage currents in the range of 500pA make these switches suitable for high precision circuits. The added feature of Break-before-Make switching allows for multiple outputs to be tied together for multiplexer applications while keeping leakage errors to a minimum.

WR	ADG221 IN	ADG222 IN	SWITCH CONDITION
0	0	1	ON
0	1	0	OFF
1	X	X	Retains Previous Switch Condition

Table I. Truth Table

ADG221/ADG222 — SPECIFICATIONS ($v_{DD} = +15V$, $v_{SS} = -15V$, unless otherwise specified)

	K Version		B Version		T Version					
Parameter	25°C	-40°C to +85°C	25°C	−40°C to +85°C	25°C	−55°C to +125°C	Units	Test Conditions		
ANALOG SWITCH Analog Signal Range R _{ON}	± 15 60 90	± 15	± 15 60 90	± 15	± 15 60 90	± 15	Volts Ω typ Ω max	$-10V \le V_S \le +10V$ $I_{DS} = 1.0 \text{mA}$ Test Circuit 1		
R_{ON} vs. $V_D(V_S)$ R_{ON} Drift R_{ON} Match	20 0.5 5		20 0.5 5		20 0.5 5		% typ %/°C typ % typ	$V_S = 0V, I_{DS} = 1mA$		
I _S (OFF) OFF Input Leakage	0.5	100	0.5 2	100	0.5 1	100	nA typ nA max	$V_D = \pm 14V; V_S \mp 14V; Test Circuit 2$		
I _D (OFF)	0.5	100	0.5	100	0.5		nA typ	$V_D = \pm 14V; V_S = \mp 14V; Test Circuit 2$		
OFF Output Leakage $I_D(ON)$ ON Channel Leakage	2 0.5 2	100 200	2 0.5 2	100 200	0.5 1	100 200	nA max nA typ nA max	$V_D = \pm 14V$; Test Circuit 3		
DIGITAL CONTROL V _{INH} , Input High Voltage V _{INL} , Input Low Voltage I _{INL} or I _{INH}		2.4 0.8 1		2.4 0.8 1		2.4 0.8 1	V min V max µA max			
DYNAMIC CHARACTERISTICS topen ton¹ toff¹ tw¹ Write Pulse Width ts¹ Digital Input Setup Time tH¹ Digital Input Hold Time OFF Isolation Channel-to-Channel Crosstalk Cs(OFF)	30 300 250 80 80	100 100 20	30 300 250 80 5	100 100 20	30 300 250 100 100 20 80	120 120 20	ns typ ns max ns max ns min ns min ns min dB typ dB typ pF typ	Test Circuit 4 Test Circuit 4 See Figure 2 See Figure 2 See Figure 2 V _S = 10V (p-p); f = 100kHz R _L = 75Ω; Test Circuit 6 Test Circuit 7		
C _S (OFF) C _D (OFF) C _D , C _S (ON) C _{IN} Digital Input Capacitance Q _{INJ} Charge Injection	5 16 5 20		5 16 5 20		5 16 5 20		pF typ pF typ pF typ pF typ pC typ	$R_S = 0\Omega; C_L = 1000pF; V_S = 0V$ Test Circuit 5		
POWER SUPPLY I _{DD} I _{DD} I _{SS} I _{SS} Power Dissipation	0.6 0.1	1.5 0.2 25.5	0.6	1.5 0.2 25.5	0.6	1.5 0.2 25.5	mA typ mA max mA typ mA max mW max	Digital Inputs = V_{INL} or V_{INH}		

ABSOLUTE MAXIMUM RATINGS* $(T_A = +25^{\circ}C \text{ unless otherwise stated})$

V_{DD} to V_{SS} .							
V_{DD} to GND							
M. CAID							

33	•
Analog Inputs ¹	
Voltage at S, D V_{SS} -0.3V t	to
$V_{\rm DD} + 0.3$	V
Continuous Current, S or D 30m.	Α
Pulsed Current S or D	
1ms Duration, 10% Duty Cycle 70m.	Α
Digital Inputs ¹	

Voltage at IN, $\sqrt[M]{R}$ V_{SS} -2V to V_{DD} +2V or 20mA, Whichever Occurs First

Power Dissipation (Any Package)

Derates above +75°C by 6mW/°C Operating Temperature Commercial (K Version) -40° C to $+85^{\circ}$ C Industrial (B Version) -40° C to $+85^{\circ}$ C Extended (T Version) -55° C to $+125^{\circ}$ C Storage Temperature $\ \ldots \ \ldots \ -65^{\circ}C$ to $\ +150^{\circ}C$ Lead Temperature (Soldering 10sec) + 300°C

Overvoltage at IN, WR, S or D will be clamped by diodes. Current should be limited to the Maximum Rating above.

-2-

. 25V

REV. B

¹Sample tested at 25°C to ensure compliance.

 t_{ON}, t_{OFF} are the same for both IN and \overline{WR} digital input changes.

Specifications subject to change without notice.

^{*}COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one Absolute Maximum Rating may be applied at any one time.

CAUTION

ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are removed.



ORDERING GUIDE

Model ¹	Temperature Range	Package Option ²
ADG221KN	$-40^{\circ}\text{C to} + 85^{\circ}\text{C}$	N-16
ADG221KR	-40°C to $+85^{\circ}\text{C}$	R-16A
ADG221KP	-40° C to $+85^{\circ}$ C	P-20A
ADG221BQ	-40° C to $+85^{\circ}$ C	Q-16
ADG221TQ	-55° C to $+125^{\circ}$ C	Q-16
ADG221TE	$-55^{\circ}\text{C to} + 125^{\circ}\text{C}$	E-20A
ADG222KN	-40° C to $+85^{\circ}$ C	N-16
ADG222KR	-40° C to $+85^{\circ}$ C	R-16A
ADG222KP	-40°C to $+85^{\circ}\text{C}$	P-20A
ADG222BQ	-40° C to $+85^{\circ}$ C	Q-16
ADG222TQ	−55°C to +125°C	Q-16
ADG222TE	−55°C to +125°C	E-20A

NOTES

¹To order MIL-STD-883, Class B processed parts, add /883B to T grade part numbers. See Analog Devices Military Products Databook (1990) for military data sheet.

²N = Plastic DIP; R = 0.15" Small Outline IC (SOIC); P = Plastic Leaded Chip Carrier (PLCC); Q = Cerdip; E = Leadless Ceramic Chip Carrier (LCCC).

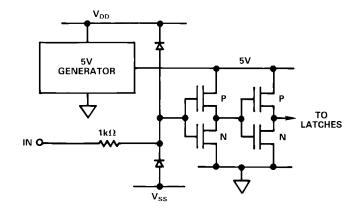
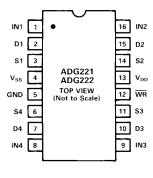
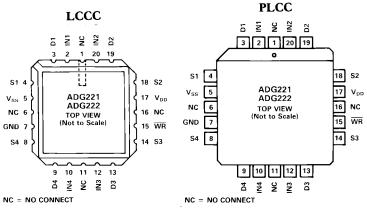


Figure 1. Typical Digital Input Cell

PIN CONFIGURATIONS

DIP, SOIC





TIMING AND CONTROL SEQUENCE

Figure 2 shows the timing sequence for latching the switch digital inputs (IN1 – IN4). The latches are level sensitive and, therefore, while \overline{WR} is held low the latches are transparent and the switches respond to the digital inputs. The digital inputs are latched on the rising edge of \overline{WR} .

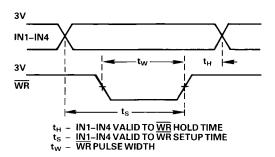
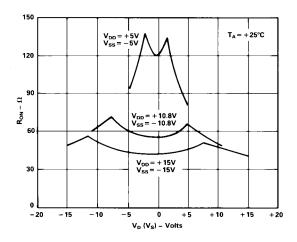


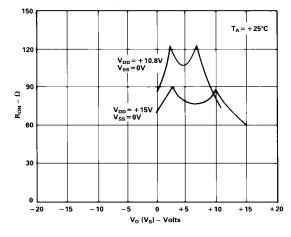
Figure 2. Timing and Control Sequence

ADG221/ADG222—Typical Performance Characteristics

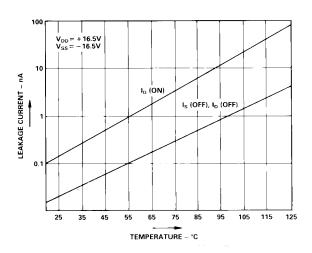
The switches are guaranteed functional with reduced single or dual supplies down to 4.5V.



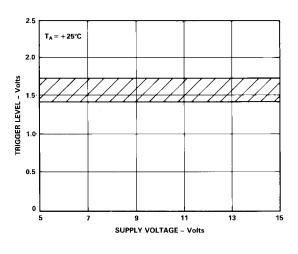
 R_{ON} as a Function of V_D (V_S): Dual Supply Voltage



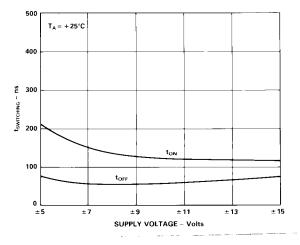
 R_{ON} as a Function of V_D (V_S): Single Supply Voltage



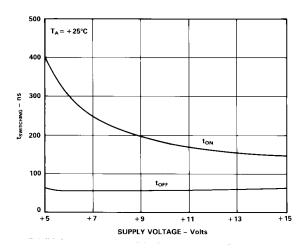
Leakage Current as a Function of Temperature (Note: Leakage Currents Reduce as the Supply Voltages Reduce)



Trigger Level vs. Power Supply Voltage: Dual or Single Supply Voltage



Switching Times vs. Supply Voltage (Dual Supply)

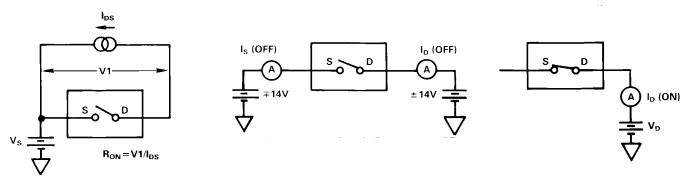


Switching Times vs. Supply Voltage (Single Supply)

REV. B

-4-

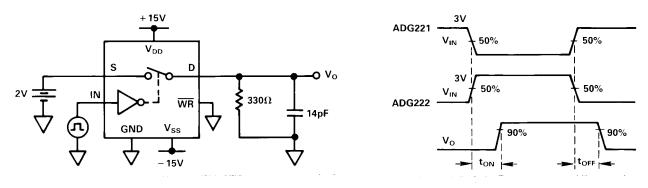
Test Circuits—ADG221/ADG222



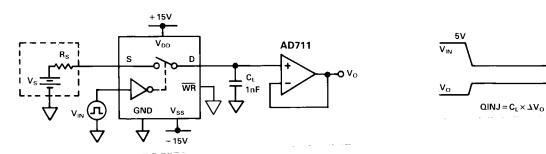
Test Circuit 1

Test Circuit 2

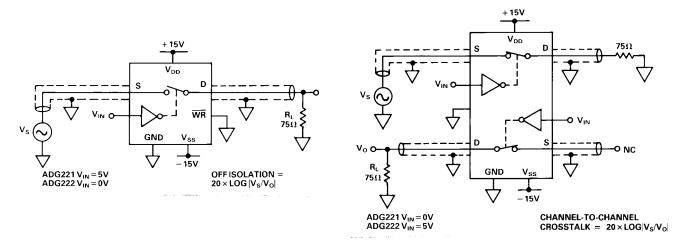
Test Circuit 3



Test Circuit 4



Test Circuit 5. Charge Injection



Test Circuit 6. Off Isolation

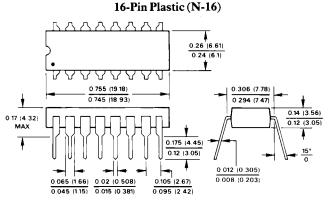
Test Circuit 7. Channel-to-Channel Crosstalk

ADG221/ADG222

TERMINOL	OGY	t_{ON}	Delay time between the 50% and 90% points of
R_{ON} R_{ON} Match I_S (OFF)	Ohmic resistance between terminals OUT and S Difference between the R _{ON} of any two channels Source terminal leakage current when the switch is off	t _{OFF}	the digital input and switch "ON" condition Delay time between the 50% and 90% points of the digital input and switch "OFF" condition "OFF" time measured between 50% points of
I_D (OFF)	Drain terminal leakage current when the switch is off		both switches, which are connected as a multi- plexer, when switching from one address state to another
$\begin{split} &I_{D}\left(ON\right) \\ &V_{D}\left(V_{S}\right) \\ &C_{S}\left(OFF\right) \\ &C_{D}\left(OFF\right) \\ &C_{IN} \\ &C_{D}, C_{S}\left(ON\right) \end{split}$	Leakage current that flows from the closed switch into the body Analog voltage on terminal D, S Switch input capacitance "OFF" condition Switch output capacitance "OFF" condition Digital input capacitance Input or output capacitance when the switch is on	$\begin{array}{c} V_{\rm INL} \\ V_{\rm INH} \\ I_{\rm INL} \left(I_{\rm INH}\right) \\ V_{\rm DD} \\ V_{\rm SS} \\ I_{\rm DD} \\ I_{\rm SS} \end{array}$	Another Maximum Input Voltage for a Logic Low Minimum Input Voltage for a Logic High Input current of the digital input Most positive voltage supply Most negative voltage supply Positive supply current Negative supply current

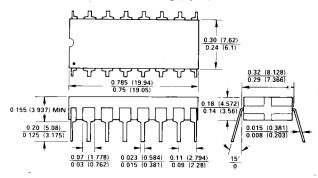
OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

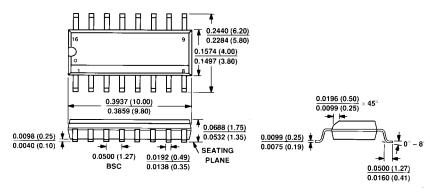


LEAD NO. 1 IDENTIFIED BY DOT OR NOTCH LEADS ARE SOLDER OR TIN-PLATED KOVAR OR ALLOY 42

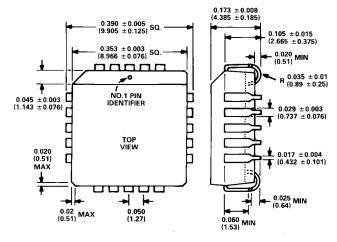
16-Pin Cerdip (Q-16)



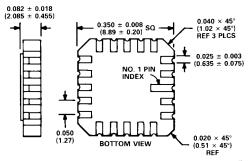
16-Lead Narrow Body SOIC (R-16A)



20-Terminal Plastic Leaded Chip Carrier (P-20A)



20-Terminal Leadless Ceramic Chip Carrier (E-20A)



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Analog Devices Inc.:

ADG221KRZ ADG221KR ADG221KNZ ADG221KPZ